

**Silicon NPN Power Transistor**

**BD637**

**DESCRIPTION**

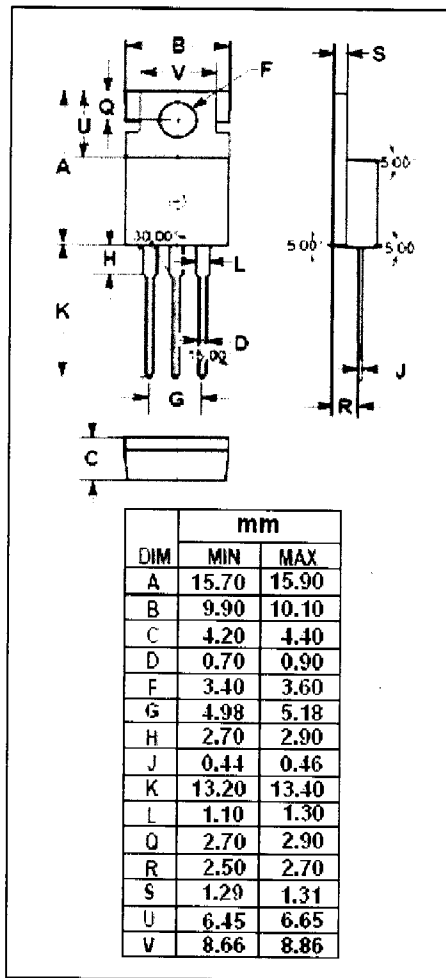
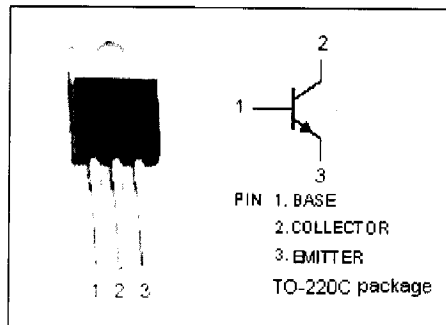
- DC Current Gain -  
 :  $h_{FE} = 40(\text{Min.}) @ I_C = 25\text{mA}$
- Collector-Emitter Breakdown Voltage -  
 :  $V_{(BR)CEO} = 80\text{V}(\text{Min.})$
- Complement to Type BD638

**APPLICATIONS**

- Designed for amplifier and switching applications.

**ABSOLUTE MAXIMUM RATINGS ( $T_a = 25^\circ\text{C}$ )**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	100	V
$V_{CEO}$	Collector-Emitter Voltage	80	V
$V_{EBO}$	Emitter-Base Voltage	5	V
$I_C$	Collector Current-Continuous	2	A
$I_{CM}$	Collector Current-Peak	5	A
$I_B$	Base Current-Continuous	0.3	A
$P_C$	Collector Power Dissipation @ $T_a = 25^\circ\text{C}$	2	W
	Collector Power Dissipation @ $T_C = 25^\circ\text{C}$	30	
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature Range	-55~150	$^\circ\text{C}$



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**Silicon NPN Power Transistor****BD637****ELECTRICAL CHARACTERISTICS****T<sub>C</sub>=25°C unless otherwise specified**

<b>SYMBOL</b>	<b>PARAMETER</b>	<b>CONDITIONS</b>	<b>MIN</b>	<b>MAX</b>	<b>UNIT</b>
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 30mA; I <sub>B</sub> = 0	80		V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> = 0.1mA; I <sub>E</sub> = 0	100		V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 1mA; I <sub>C</sub> = 0	5		V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 1A; I <sub>B</sub> = 0.1A		0.6	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	I <sub>C</sub> = 1A; V <sub>CE</sub> = 2V		1.3	V
I <sub>CES</sub>	Collector Cutoff Current	V <sub>CE</sub> = 100V; V <sub>BE</sub> = 0		0.2	mA
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 25mA; V <sub>CE</sub> = 2V	40		
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 1A; V <sub>CE</sub> = 2V	25		